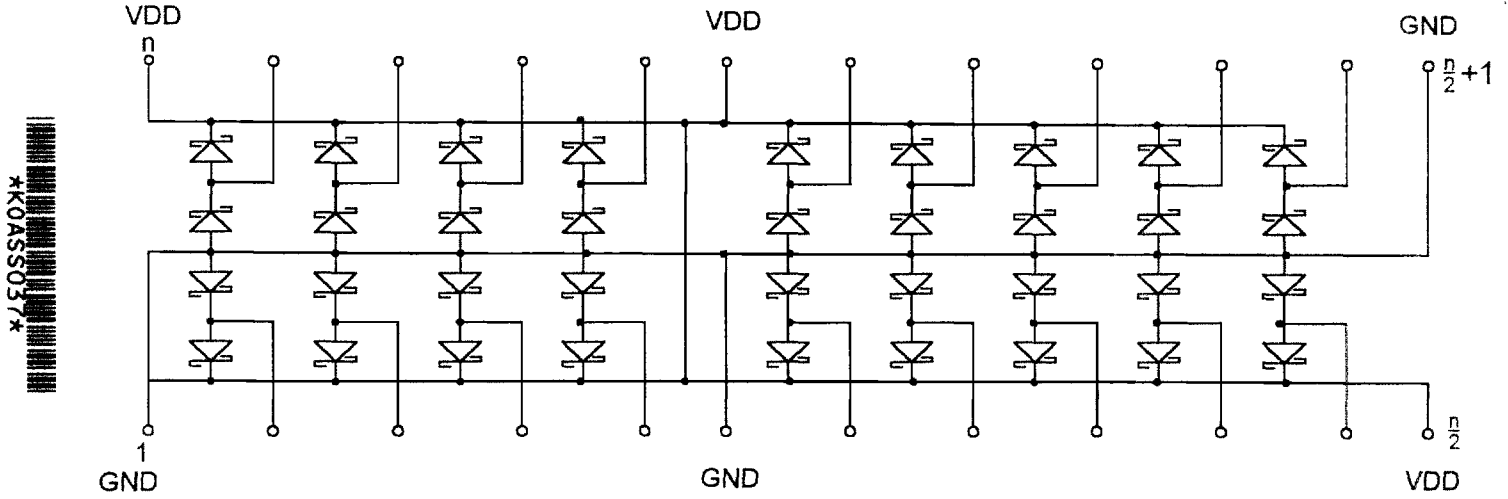


SCHEMATIC



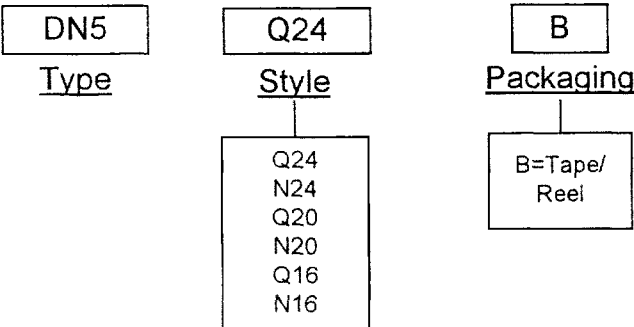
STANDARD SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating
Supply Voltage	VDD	-0.3V to +7V
Channel clamp current (continuous)	I _{clamp}	±50mA
Power Dissipation, T _a =25°C.		900mW
Operating Temperature		0°C to 70°C.
Storage Temperature	T _{stg}	-65°C to +150°C
Package Power Rating		1.00W, max.

DIODE CHARACTERISTICS (T_A = 0° to 70°C)

Parameter	Conditions	Min	Type	Max
Diode forward voltage	I _F = 16mA		0.5V	0.65V
	I _F = 50mA	0.5V	0.65V	0.85V
Channel leakage	0 ≤ V _{in} ≤ VDD		0.1μA	5μA
Input Capacitance	f = 1MHz, V _{in} = 2.5V, T _A = 25°C.		5pF	
ESD Protection	MIL-STD-883, Method 3015	4KV		



Styles Available:

- 24 Pin QSOP.....Q24
- 24 Pin Narrow SOIC.....N24
- 20 Pin QSOP.....Q20
- 20 Pin Narrow SOIC.....N20
- 16 Pin QSOP.....Q16
- 16 Pin Narrow SOIC.....N16